STATIC RANDOM ACCESS MEMORY DEVICE HAVING DECREASED SENSITIVITY TO VARIATIONS IN CHANNEL PHYSICAL CHARACTERISTICS

ABSTRACT OF THE DISCLOSURE

A static random access memory (SRAM) device and a method of manufacturing the same. In one embodiment, the SRAM device includes: (1) a first bias voltage contact biasable to a first potential, (2) a second bias voltage contact biasable to a second potential that differs from the first potential and (3) a well having channels formed therein and connected to one of said first and second bias voltage contacts based on a transistor characteristic of said SRAM device that bears on static noise margin (SNM) and write trip voltage V_{trip}.